

ATP401

N-Channel Power MOSFET 60V, 100A, 3.7mΩ, ATPAK

Features

- resistance $R_{DS(on)}$ 1=2.8mΩ(typ)
- 4.5V Drive
- Input Capacitance C_{iss} =17000pF(typ)
- Halogen free compliance

Specifications

Absolute Maximum Ratings at $T_a=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		60	V
Gate-to-Source Voltage	V_{GS}		±20	V
Drain Current (DC)	I_D		100	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	400	A
Allowable Power Dissipation	P_D	$T_c=25^{\circ}\text{C}$	90	W
Channel Temperature	T_{ch}		150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^{\circ}\text{C}$
Avalanche Energy (Single Pulse) *1	E_{AS}		549	mJ
Avalanche Current *2	I_{AV}		70	A

*1 $V_{DD}=36\text{V}$, $L=100\mu\text{H}$, $I_{AV}=70\text{A}$ (Fig.1)

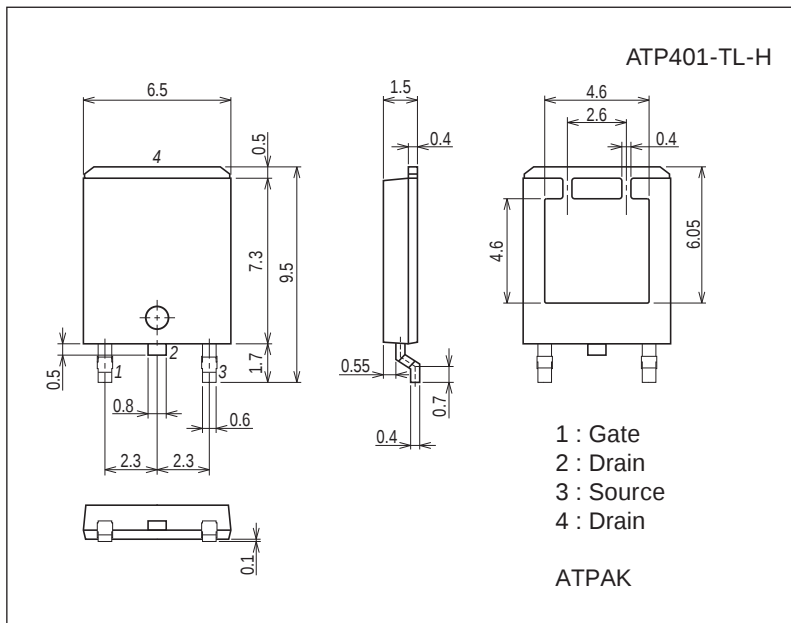
*2 $L \leq 100\mu\text{H}$, Single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

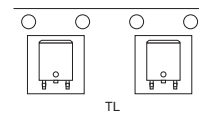
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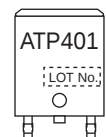
Product & Package Information

- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

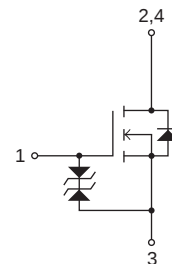
Packing Type: TL



Marking



Electrical Connection



ATP401

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	60			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	1.2		2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=50A$		90		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=50A, V_{GS}=10V$		2.8	3.7	$m\Omega$
	$R_{DS(on)2}$	$I_D=50A, V_{GS}=4.5V$		3.7	5.2	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=20V, f=1MHz$		17000		pF
Output Capacitance	C_{oss}			1000		pF
Reverse Transfer Capacitance	C_{rss}			770		pF
Turn-ON Delay Time	$t_d(on)$	See Fig.2		110		ns
Rise Time	t_r			580		ns
Turn-OFF Delay Time	$t_d(off)$			840		ns
Fall Time	t_f			710		ns
Total Gate Charge	Q_g	$V_{DS}=36V, V_{GS}=10V, I_D=100A$		300		nC
Gate-to-Source Charge	Q_{gs}			60		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			60		nC
Diode Forward Voltage	V_{SD}	$I_S=100A, V_{GS}=0V$		0.9	1.2	V

Fig.1 Unclamped Inductive Switching Test Circuit

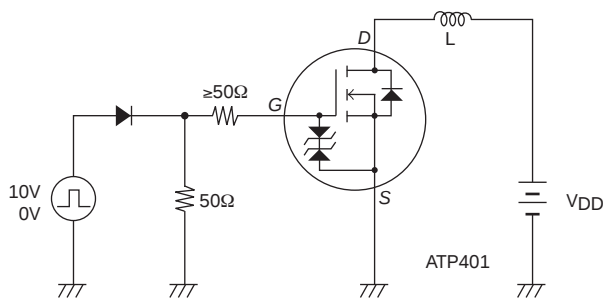
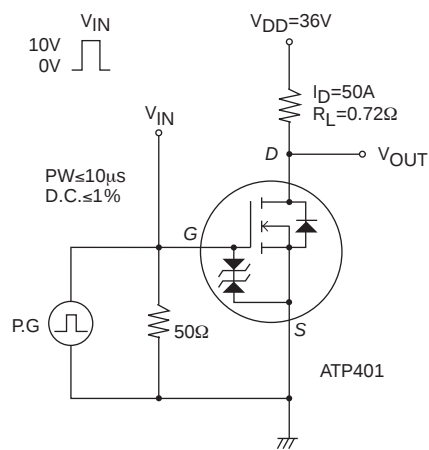
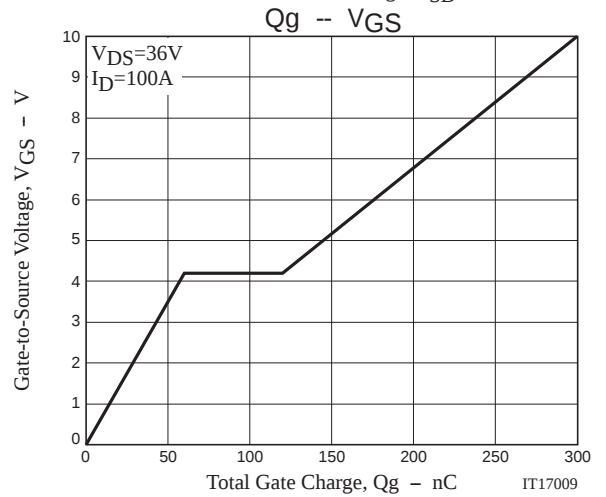
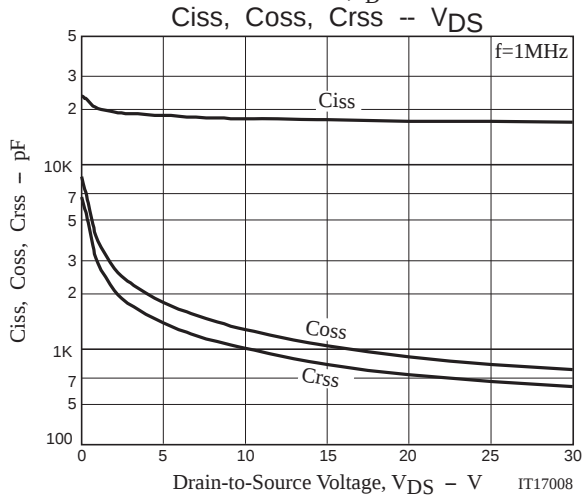
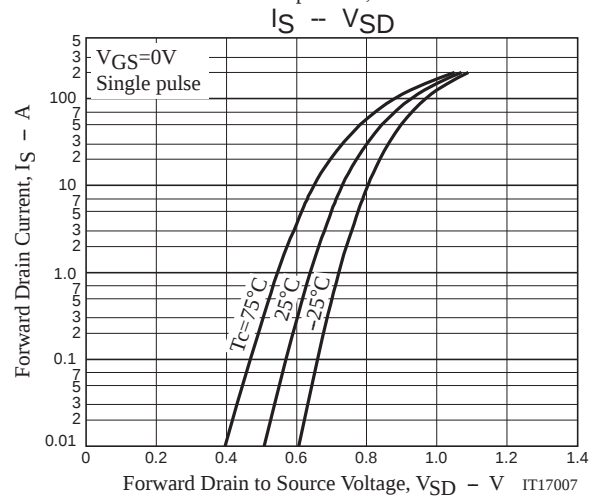
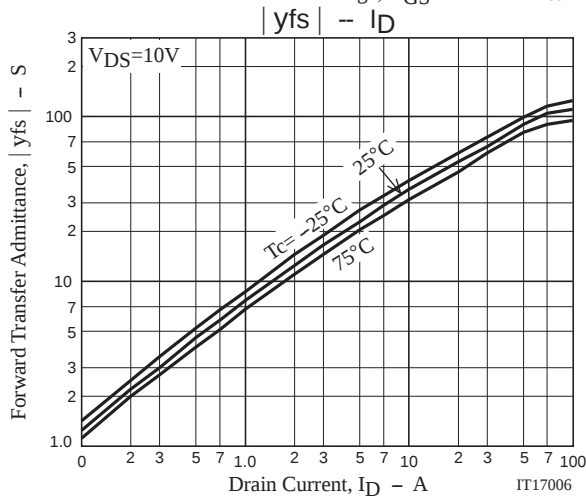
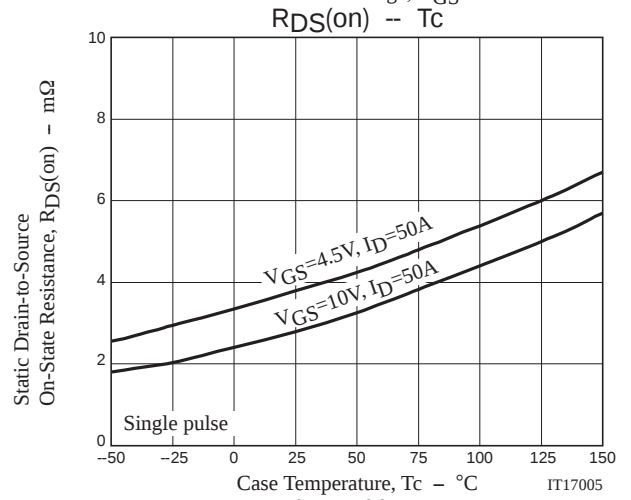
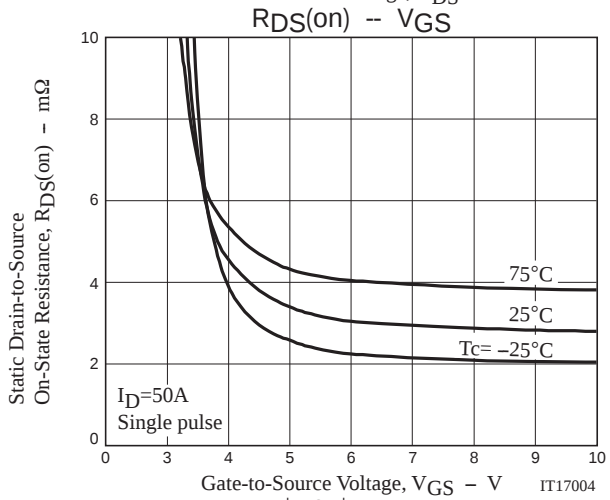
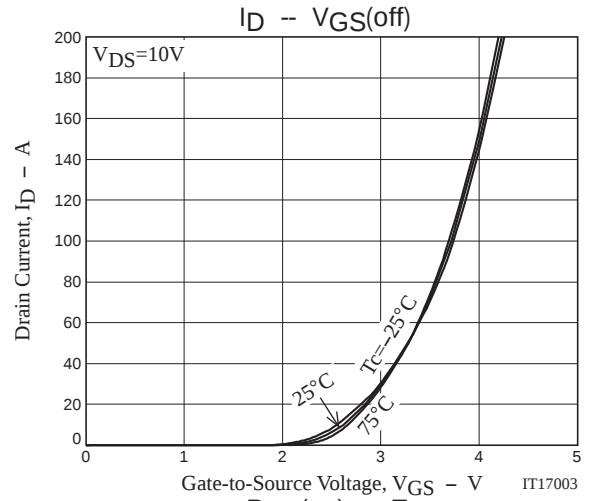
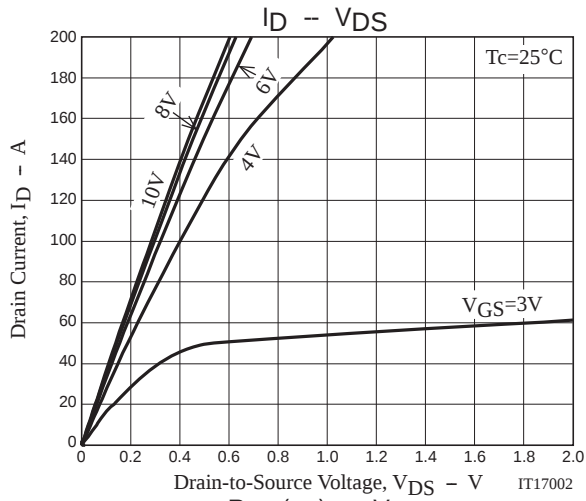


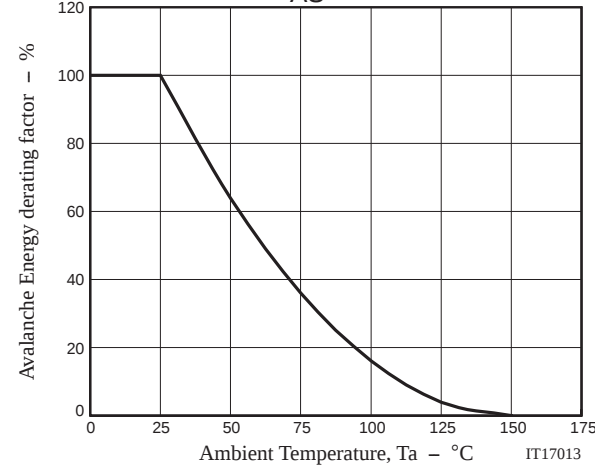
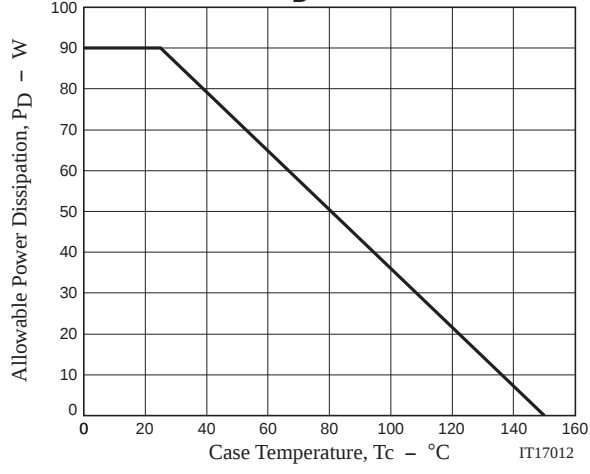
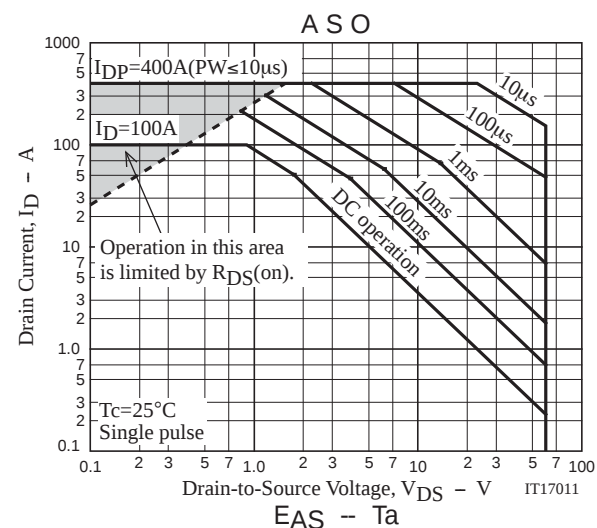
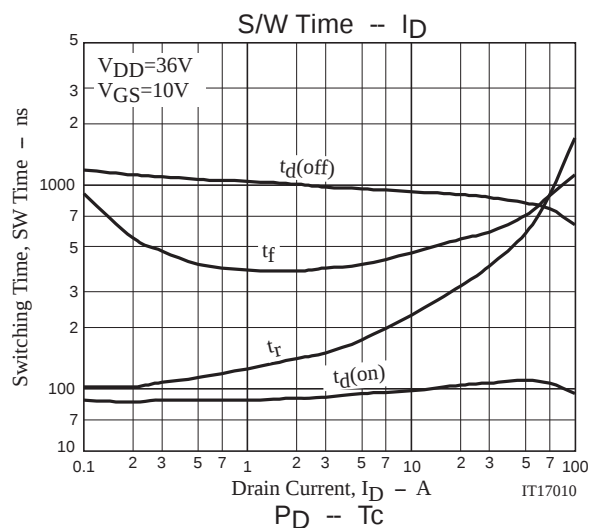
Fig.2 Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
ATP401-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free





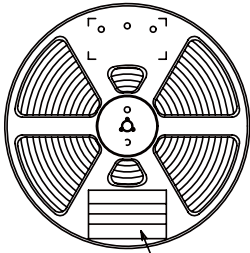
Taping Specification

ATP401-TL-H

1. Packing Format (TL)

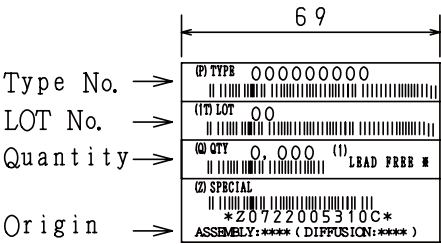
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18
ATPAK	ATP	3,000	3,000	15,000	1 reels contained Dimensions:mm (external) 340×340×28	5 inner boxes contained Dimensions:mm (external) 355×355×165

Packing method



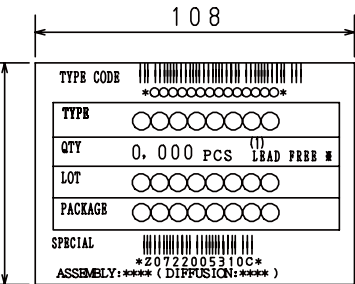
Reel label

Reel label, Inner box label
(unit:mm)



Outer box label

It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.



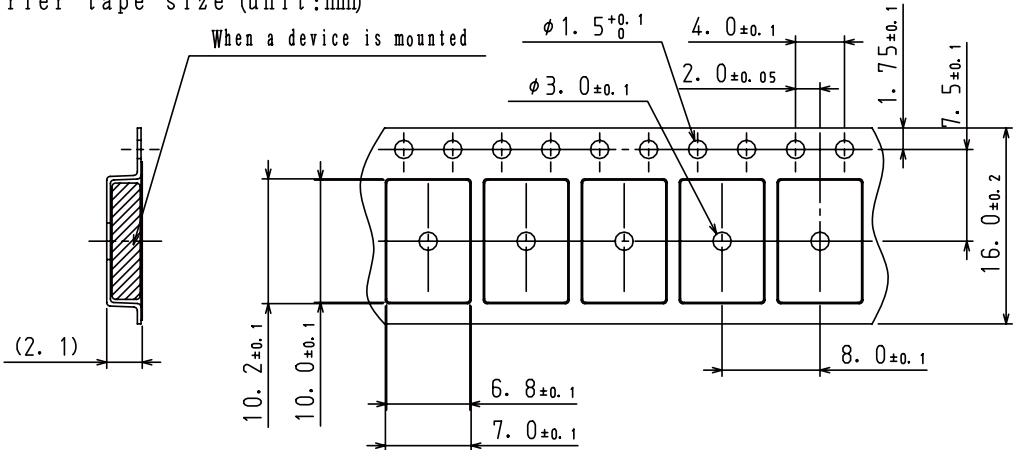
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

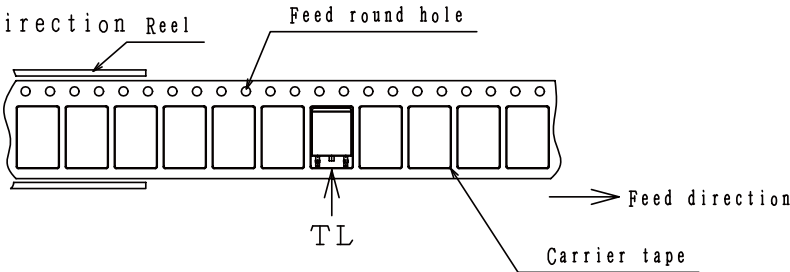
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)

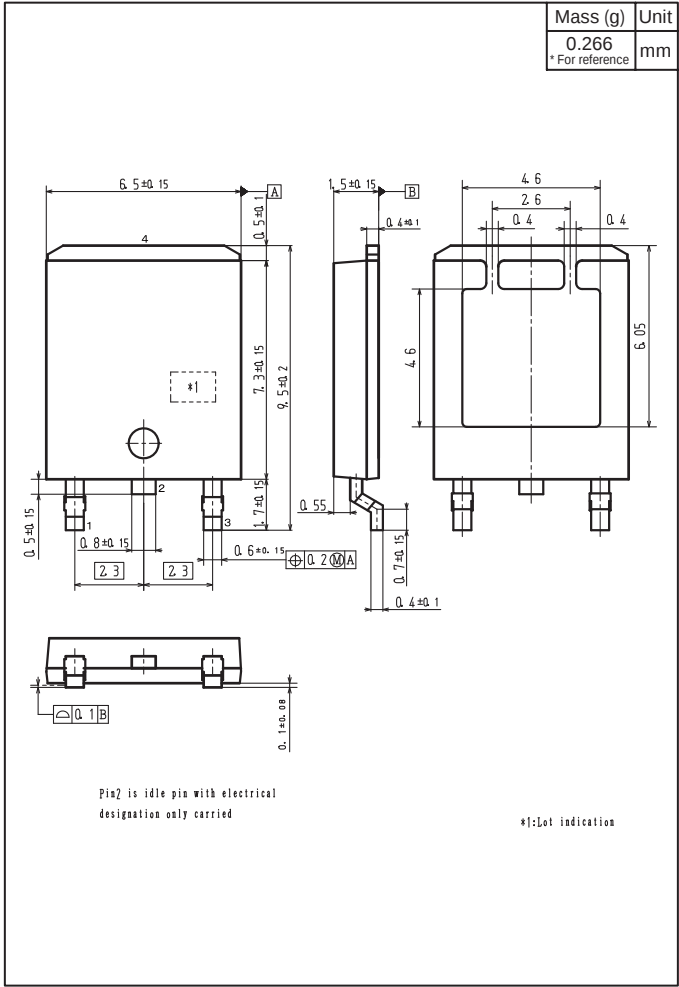


2-2. Device placement direction Reel



The one electrode terminals on feed hole side...TL

Outline Drawing
ATP401-TL-H



Land Pattern Example

